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## DG2731/2732/2733

Vishay Siliconix

### Low Voltage, 0.4 $\Omega$ , Dual SPDT Analog Switch

#### DESCRIPTION

The DG2731/2732/2733 are low voltage, low on-resistance, dual single-pole/double-throw (SPDT) monolithic CMOS analog switches designed for high performance switching of analog signals. Combining low-power, high speed, low on-resistance, and small package size, the DG2731/2732/2733 are ideal for portable and battery power applications.

The DG2731/2732/2733 have an operation range from 1.6 V to 4.3 V single supply. The DG2731 and DG2732 have two separate control pins with reverse control logic. The DG2733 has an EN pin to enable the device when the logic is high.

The DG2731/2732/2733 are 1.6-V logic compatible, allowing the easy interface with low voltage DSP or MCU control logic and ideal for one cell Li-ion battery direct power.

The switch conducts signals within power rails equally well in both directions when on, and blocks up to the power supply level when off. Break-before-make is guaranteed.

The DG2731/2732/2733 are built on Vishay Siliconix's sub micron CMOS low voltage process technology and provides greater than 300 mA latch-up protection, as tested per JESD78.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations. DG2731/2732/2733 are offered in a DFN or MSOP package. The DFN package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix. The MSOP package uses 100% matte Tin device termination and is represented by the lead (Pb)-free "-E3" suffix. Both the matte Tin and nickel-palladium-gold device terminations meet all JEDEC standards for reflow and MSL ratings.

#### FEATURES

- Low Voltage Operation (1.65 V to 4.3 V)
- Low On-Resistance -  $r_{ON}$ : 0.3  $\Omega$  @ 3.6 V
- Fast Switching:  $T_{ON}$  = 50 ns @ 4.3 V
- $T_{OFF}$  = 14 ns @ 4.3 V
- Latch-Up Current > 300 mA (JESD78)

#### BENEFITS

- Reduced Power Consumption
- High Accuracy
- Reduce Board Space
- TTL/1.6-V Logic Compatible

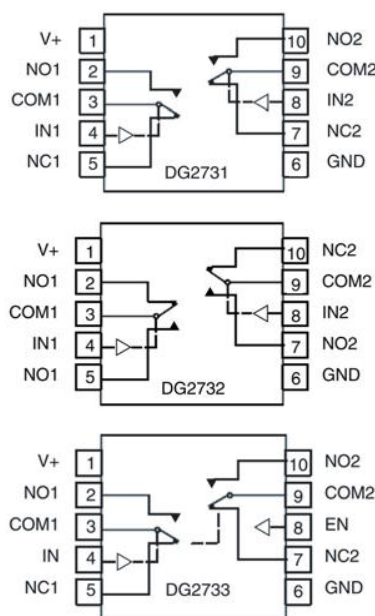
#### APPLICATIONS

- Cellular Phones
- Speaker Headset Switching
- Audio and Video Signal Routing
- PCMCIA Cards
- Battery Operated Systems



**RoHS**  
COMPLIANT

#### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



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TRUTH TABLE			
Logic	EN (DG2733 only)	NC1, 2	NO1, 2
0	1	ON	OFF
1	1	OFF	ON
0	0	OFF	OFF
1	0	OFF	OFF

ORDERING INFORMATION		
Temp Range	Package	Part Number
-40 to 85°C	MSOP-10	DG2731DQ-T1-E3 DG2732DQ-T1-E3 DG2733DQ-T1-E3
	DFN-10	DG2731DN-T1-E4 DG2732DN-T1-E4 DG2733DN-T1-E4

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Reference to GND	V+	-0.3 to 5.0	V	
	IN, COM, NC, NO <sup>a</sup>	-0.3 to (V <sup>+</sup> + 0.3)		
Current (Any terminal except NO, NC or COM)		30	mA	
Continuous Current (NO, NC, or COM)		±250		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		±500		
Storage Temperature (D Suffix)		-65 to 150	°C	
Package Solder Reflow Conditions <sup>d</sup>	10-PIN MSOP			
	10-PIN DFN			
Power Dissipation (Packages) <sup>b</sup>	MSOP-10 <sup>c</sup>	320	mW	
	DFN-10 <sup>d</sup>	1191		

## Notes

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.  
b. All leads welded or soldered to PC Board.  
c. Derate 4.0 mW/C above 70°C  
d. Derate 14.9 mW/C above 70°C  
e. Manual soldering with iron is not recommended for leadless components. The QFN is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

SPECIFICATIONS (V+ = 1.8 V)							
Parameter	Symbol	Test Condition Otherwise Unless Specified V+ = 1.8 V, V <sub>IN</sub> = 0.4 or 1.4 V <sup>e</sup>	Temp <sup>a</sup>	Limits −40 to 85°C			Unit
				Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	V <sub>NO</sub> , V <sub>NC</sub> , V <sub>COM</sub>		Full	0		V+	V
On-Resistance	r <sub>ON</sub>	V+ = 1.8 V, V <sub>COM</sub> = 0.9 V, I <sub>NO</sub> , I <sub>NC</sub> = 100 mA	Room		0.7	1.0	Ω
			Full			1.2	
Digital Control							
Input High Voltage	V <sub>INH</sub>		Full	1.4			V
Input Low Voltage	V <sub>INL</sub>		Full			0.4	
Input Capacitance	C <sub>in</sub>		Full		4		pF
Power Supply							
Power Supply Current	I+	V <sub>IN</sub> = 0 or V+	Full			1.0	μA



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SPECIFICATIONS (V+ = 3 V)							
Parameter	Symbol	Test Condition Otherwise Unless Specified V+ = 3 V, ±10 %, VIN = 0.5 or 1.4 V <sup>e</sup>	Temp <sup>a</sup>	Limits −40 to 85°C			Unit
				Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance	rON	V+ = 2.7 V, VCOM = 0.5 V, INO, INC = 100 mA	Room		0.35	0.45	Ω
		V+ = 2.7 V, VCOM = 1.5 V, INO, INC = 100 mA			0.3		
			Full			0.6	
rON Match <sup>d</sup>	ΔrON	V+ = 2.7 V, VCOM = 0.5 to 1.5 V, INO, INC = 100 mA	Room		0.03	0.06	
Switch Off Leakage Current	INO(off), INC(off)	V+ = 3.3 V, VNO, VNC = 0.3 V / 4.0 V, VCOM = 3.0 V / 0.3 V	Room Full	−1 −10		1 10	nA
	ICOM(off)		Room Full	−1 −10		1 10	
Channel-On Leakage Current	ICOM(on)	V+ = 3.3 V, VNO, VNC = VCOM = 3.0 V / 0.3 V	Room Full	−1 −10		1 10	
Digital Control							
Input High Voltage	VINH		Full	1.4			V
Input Low Voltage	VINL		Full			0.5	
Input Capacitance	Cin		Full		5		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	−1		1	μA
Dynamic Characteristics							
Turn-On Time	tON	V+ = 3.6 V VNO or VNC = 1.5 V, RL = 50 Ω, CL = 35 pF	Room Full		85	110 140	ns
Turn-Off Time	tOFF		Room Full		17	30 35	
Break-Before-Make Time	tBBM		Full	10			
Charge Injection <sup>d</sup>	QINJ	CL = 1 nF, VGEN = 0 V, RGEN = 0 Ω	Room		9		pC
Off-Isolation <sup>d</sup>	OIRR	RL = 50 Ω, CL = 5 pF, f = 100 kHz	Room		−75		dB
Crosstalk <sup>d</sup>	XTALK		Room		−75		
NO, NC Off Capacitance <sup>d</sup>	CNO(off)	VIN = 0 or V+, f = 1 MHz	Room		104		pF
	CNC(off)		Room		104		
Channel On Capacitance <sup>d</sup>	CNO(on)		Room		230		
	CNC(on)		Room		230		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	I+	VIN = 0 or V+	Full			1.0	μA
Turn-On Time DG2733 (EN)	tON(EN)	V+ = 3.6 V VNO or VNC = 1.5 V, RL = 50 Ω, CL = 35 pF	Room Full		79	105 135	ns
Turn-Off Time DG2733 (EN)	tOFF(EN)		Room Full		17	29 35	

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SPECIFICATIONS (V+ = 4.3 V)							
Parameter	Symbol	Test Condition Otherwise Unless Specified V+ = 4.3 V, VIN = 0.5 or 1.6 V <sup>e</sup>	Temp <sup>a</sup>	Limits –40 to 85°C			Unit
				Min <sup>b</sup>	Typ <sup>c</sup>	Max <sup>b</sup>	
Analog Switch							
Analog Signal Range <sup>d</sup>	VNO, VNC, VCOM		Full	0		V+	V
On-Resistance	rON	V+ = 4.3 V, VCOM = 0.9 V, INO, INC = 100 mA	Room		0.29	0.4	Ω
		V+ = 4.3 V, VCOM = 2.5 V, INO, INC = 100 mA			0.21		
			Full			0.55	
rON Match <sup>d</sup>	ΔrON	V+ = 4.3 V, VCOM = 0.9 to 2.5 V+, INO, INC = 100 mA	Room		0.03	0.06	
Switch Off Leakage Current <sup>d</sup>	INO(off), INC(off)	V+ = 4.3 V, VNO, VNC = 0.3 V / 4.0 V, VCOM = 4.0 V / 0.3 V	Full	–20		20	nA
	ICOM(off)		Full	–20		20	
Channel-On Leakage Current <sup>d</sup>	ICOM(on)	V+ = 4.3 V, VNO, VNC = VCOM = 3.0 V / 4.0 V	Full	–20		20	
Digital Control							
Input High Voltage	VIN		Full	1.6			V
Input Low Voltage	VINL		Full			0.5	
Input Capacitance	Cin		Full		–4		pF
Input Current	IINL or IINH	VIN = 0 or V+	Full	–1		1	μA
Dynamic Characteristics							
Break-Before-Make Time	tBBM	VNO or VNC = 1.5 V, RL = 50 Ω, CL = 35 pF	Full	5			ns
Power Supply							
Power Supply Range	V+					4.3	V
Power Supply Current	I+	VIN = 0 or V+	Full			1.0	μA

## Notes

a. Room = 25°C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, not subjected to production test.

e. V<sub>IN</sub> = input voltage to perform proper function.

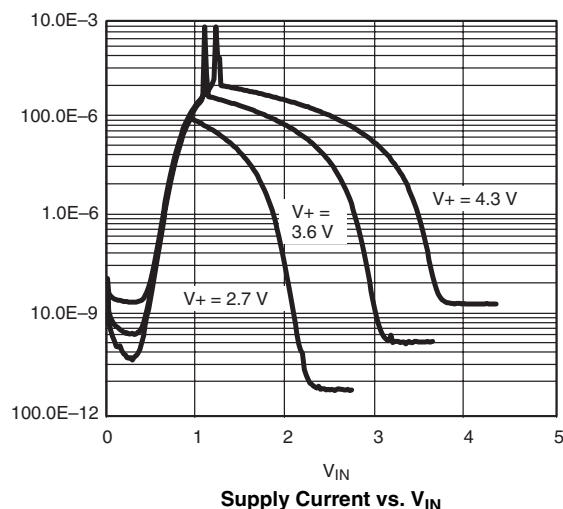
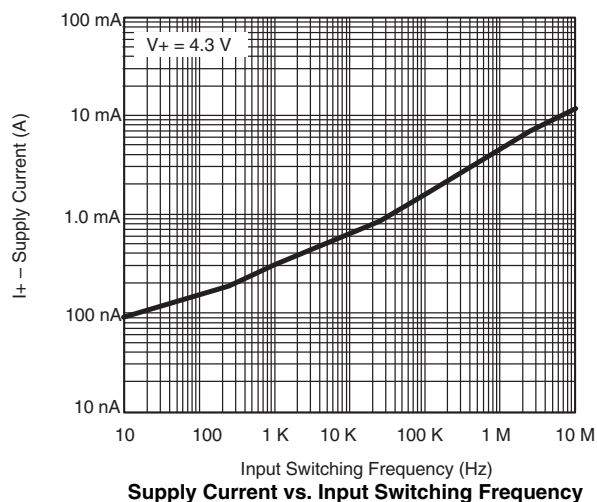
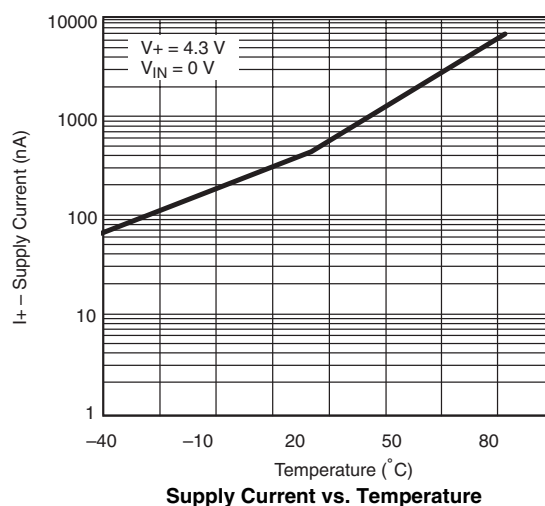
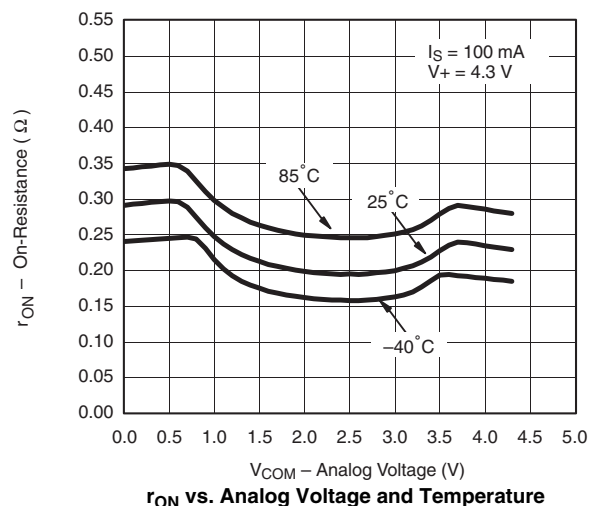
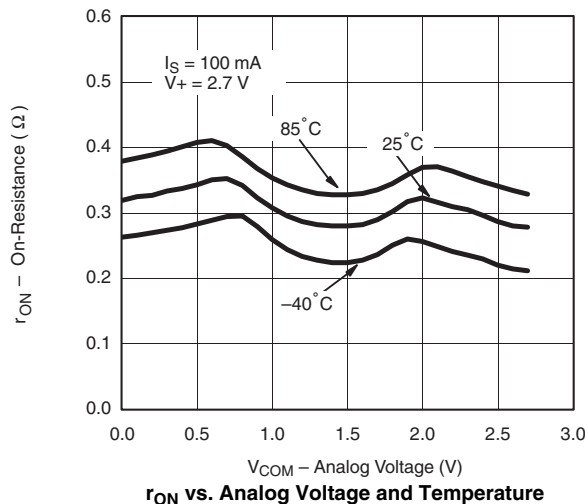
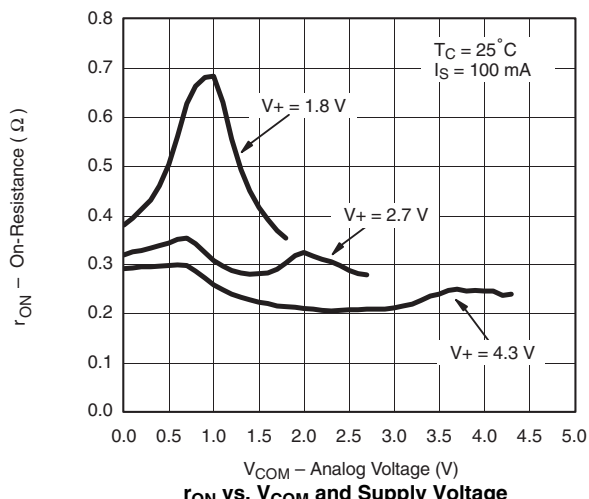
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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## TYPICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ , unless otherwise noted

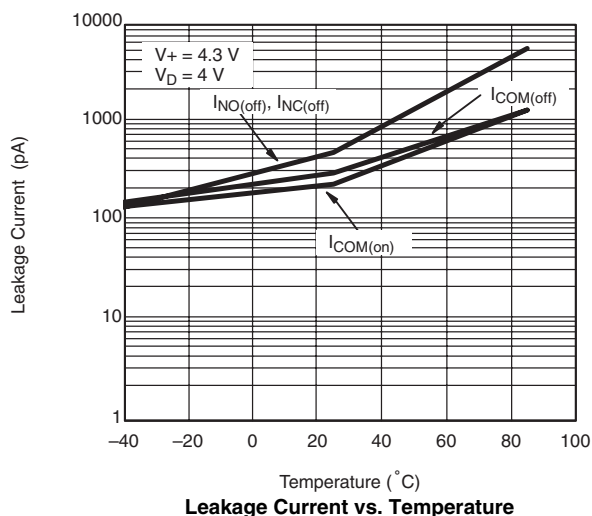


## DG2731/2732/2733

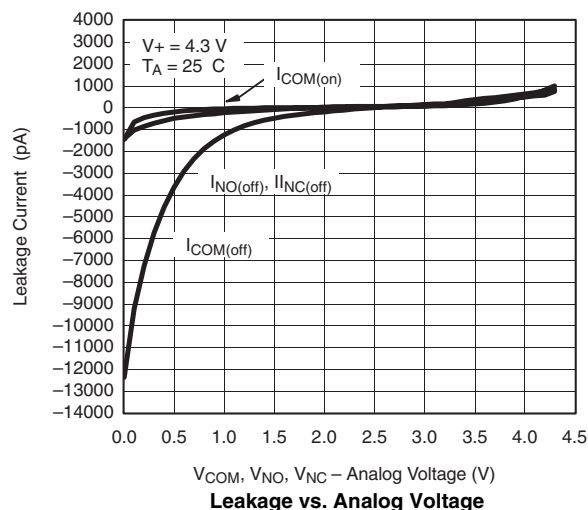
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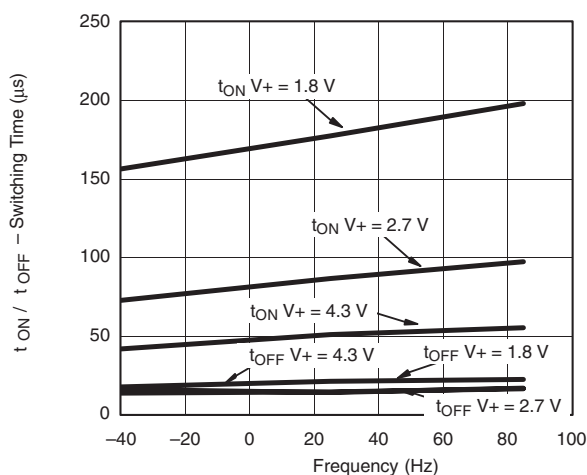
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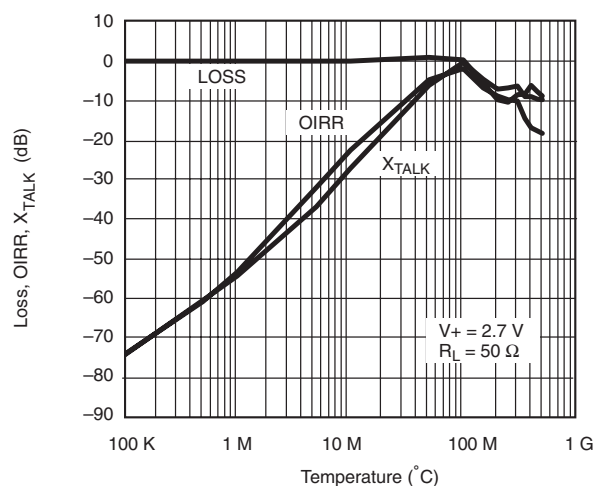
**Leakage Current vs. Temperature**



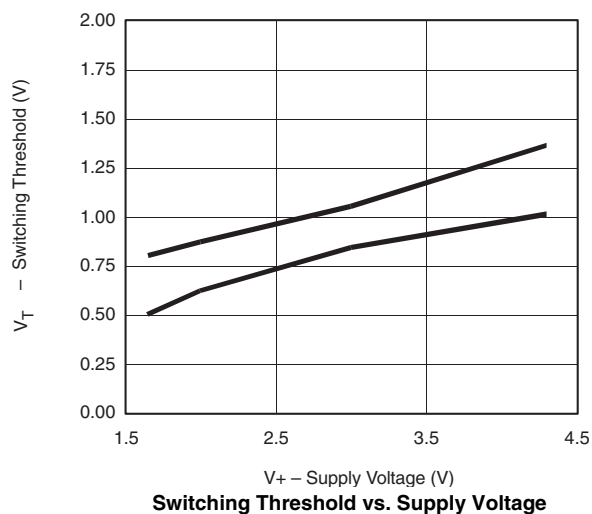
**Leakage vs. Analog Voltage**



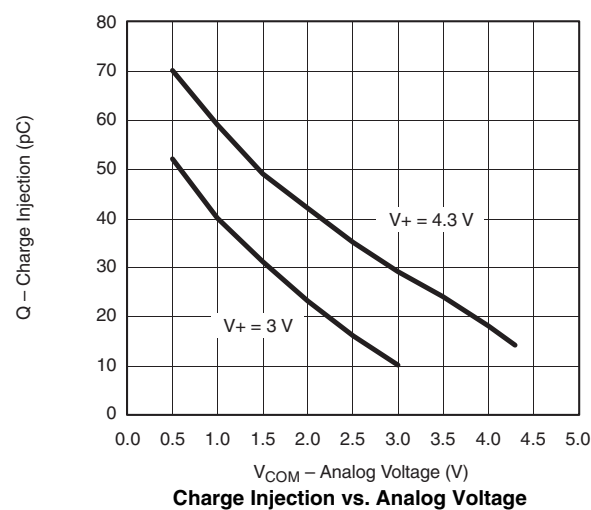
**Switching Time vs. Temperature**



**Insertion Loss, Off-Isolation Crosstalk vs. Frequency**



**Switching Threshold vs. Supply Voltage**



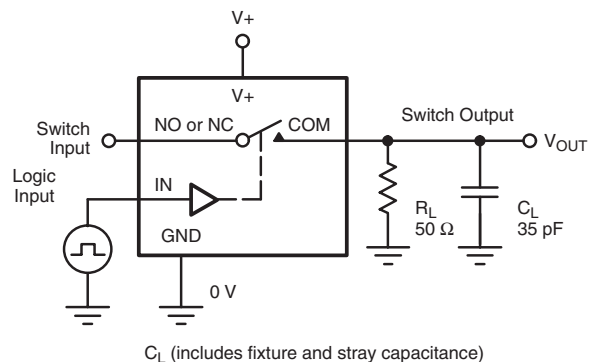
**Charge Injection vs. Analog Voltage**



**DG2731/2732/2733**

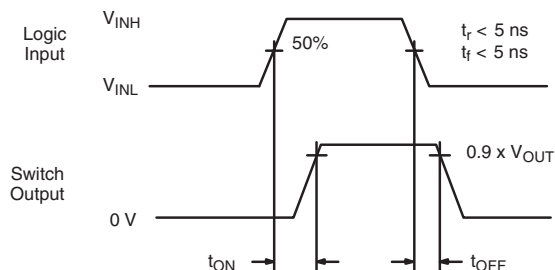
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## TEST CIRCUITS

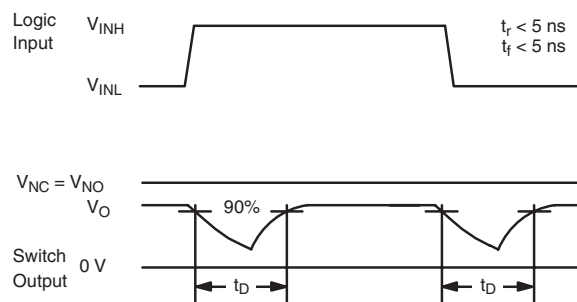
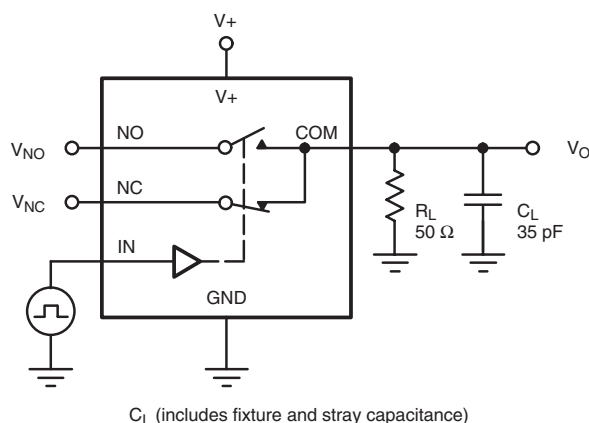


$$V_{OUT} = V_{COM} \left( \frac{R_L}{R_L + R_{ON}} \right)$$

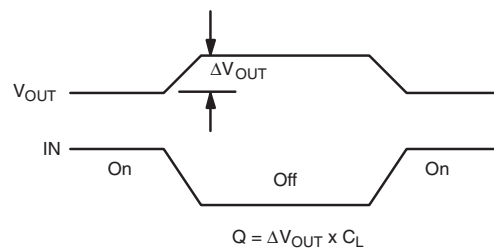
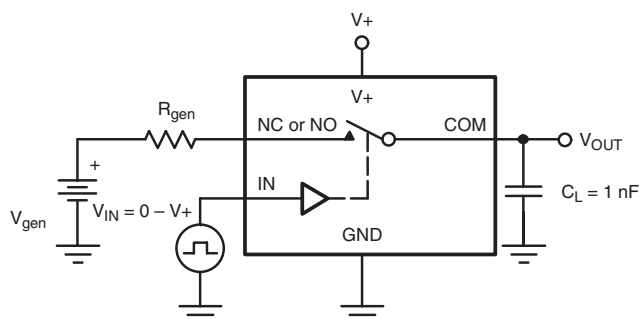
**Figure 1. Switching Time**



Logic "1" = Switch On  
Logic input waveforms inverted for switches that have the opposite logic sense.



**Figure 2. Break-Before-Make Interval**



IN depends on switch configuration: input polarity determined by sense of switch.

**Figure 3. Charge Injection**



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### TEST CIRCUITS

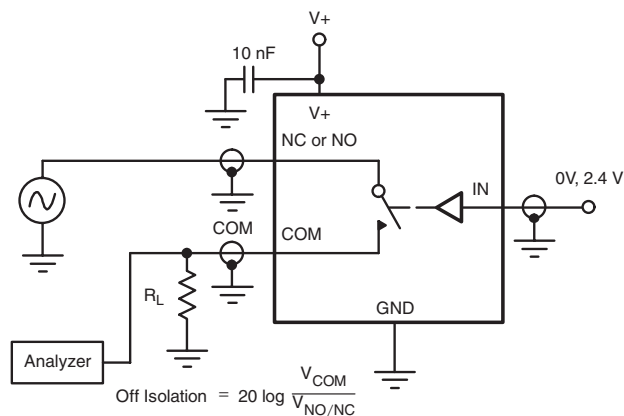


Figure 4. Off-Isolation

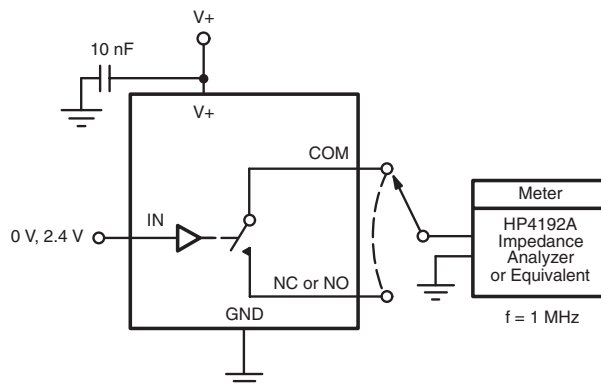


Figure 5. Channel Off/On Capacitance

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